Robert F Davis

List of Publications by Year
in descending order

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449 papers	19,825 citations	9756 73 h-index	16605 123 g-index
454 all docs	454 docs citations	454 times ranked	10284 citing authors

#	Article	IF	Citations
1	Layered phase composition and microstructure of Î²-Ga2O3-dominant heteroepitaxial films grown via MOCVD. Journal of Applied Physics, 2022, 131, .	1.1	12
2	Flow-modulated deposition of sp²-boron nitride using diborane and ammonia on chemomechanically polished (0001) 4H-SiC substrates. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2022, 40, 023409.	0.9	1
3	Chemical vapor deposition of sp²-boron nitride on mechanically polished pyrolytic boron nitride substrates. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2022, 40, 042203.	0.9	0
4	On the discrepancies between the experimental realization and the thermodynamic predictions of stability of rhombohedral boron nitride. MRS Communications, 2021, 11, 451-456.	0.8	0
5	Progression of central nervous system disease from pediatric to young adulthood in sickle cell anemia. Experimental Biology and Medicine, 2021, 246, 2473-2479.	1.1	4
6	Thermodynamic calculations for the chemical vapor deposition of hexagonal boron nitride using triethylboron, ammonia, and hydrogen. Journal of Crystal Growth, 2021, 572, 126283.	0.7	3
7	Characterization of Epitaxial Î²-(Al,Ga,In)2O3-Based Films and Applications as UV Photodetectors. Journal of Electronic Materials, 2020, 49, 3490-3498.	1.0	15
8	Metal Organic Chemical Vapor Deposition 2. Springer Series in Materials Science, 2020, , 171-184.	0.4	0
9	Nondiffusive electron transport in metals: A two-temperature Boltzmann transport equation analysis of thermoreflectance experiments. Physical Review B, 2019, 99, .	1.1	1
10	Progression of Central Nervous System Vasculopathy in Young Adults with Sickle Cell Anemia. Blood, 2019, 134, 2290-2290.	0.6	0
11	Growth and characterization of Î±-, Î²-, and Ïµ-phases of Ga₂O₃ using MOCVD and HVPE techniques. Materials Research Letters, 2018, 6, 268-275.	4.1	163
12	Electrical behavior of Î²-Ga2O3 Schottky diodes with different Schottky metals. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2017, 35, .	0.6	115
13	Investigation of Different Metals as Ohmic Contacts to Î²-Ga2O3: Comparison and Analysis of Electrical Behavior, Morphology, and Other Physical Properties. Journal of Electronic Materials, 2017, 46, 2053-2060.	1.0	96
14	(Invited) Growth and Characterization ofÎ±-,Î²-, andÎµ-Ga₂O₃Epitaxial Layers on Sapphire. ECS Transactions, 2017, 80, 191-196.	0.3	28
15	Organometallic Vapor Phase Epitaxial Growth of Group III Nitrides â˜†. , 2017, , .		0
16	(Invited) Growth and Characterization of Î±-, Î²-, and Îµ-Ga2O3 Epitaxial Layers on Sapphire. ECS Meeting Abstracts, 2017, , .	0.0	0
17	Polymer ligandâ€“induced autonomous sorting and reversible phase separation in binary particle blends. Science Advances, 2016, 2, e1601484.	4.7	30
18	Thermal interface conductance across metal alloyâ€“dielectric interfaces. Physical Review B, 2016, 93, .	1.1	20

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19	Analysis of compositional uniformity in AlxGa1â˜'xN thin films using atom probe tomography and electron microscopy. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, .	0.9	5
20	Substrates and epitaxial deposition processes for Group III-nitride thin films and power device heterostructures. MRS Bulletin, 2015, 40, 406-411.	1.7	1
21	Photoemission investigation of the Schottky barrier at the Sc/3C-SiC (111) interface. Physica Status Solidi (B): Basic Research, 2015, 252, 391-396.	0.7	11
22	Hydrogen desorption from hydrogen fluoride and remote hydrogen plasma cleaned silicon carbide (0001) surfaces. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2015, 33, .	0.9	7
23	Cleaning of pyrolytic hexagonal boron nitride surfaces. Surface and Interface Analysis, 2015, 47, 798-803.	0.8	10
24	Band alignment at AlN/Si (111) and (001) interfaces. Journal of Applied Physics, 2015, 118, .	1.1	8
25	Hydrogen desorption kinetics for aqueous hydrogen fluoride and remote hydrogen plasma processed silicon (001) surfaces. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2015, 33, .	0.9	6
26	Valence and conduction band alignment at ScN interfaces with 3C-SiC (111) and 2H-GaN (0001). Applied Physics Letters, 2014, 105, 081606.	1.5	14
27	Desorption and sublimation kinetics for fluorinated aluminum nitride surfaces. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2014, 32, .	0.9	9
28	Site-specific comparisons of V-defects and threading dislocations in InGaN/GaN multi-quantum-wells grown on SiC and GaN substrates. Journal of Crystal Growth, 2014, 387, 16-22.	0.7	12
29	Gas source molecular beam epitaxy of scandium nitride on silicon carbide and gallium nitride surfaces. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2014, 32, .	0.9	38
30	Composition and interface analysis of InGaN/GaN multiquantum-wells on GaN substrates using atom probe tomography. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, 051209.	0.6	10
31	Rugged Electrical Power Switching in Semiconductors: A Systems Approach. Proceedings of the IEEE, 2014, 102, 35-52.	16.4	16
32	Universal phonon mean free path spectra in crystalline semiconductors at high temperature. Scientific Reports, 2013, 3, 2963.	1.6	125
33	Modeling the Electrical Response of Hydrogen Sensors Based on AlGaN/GaN High-Electron-Mobility Transistors. ECS Journal of Solid State Science and Technology, 2013, 2, Q214-Q219.	0.9	3
34	The impact of film thickness and substrate surface roughness on the thermal resistance of aluminum nitride nucleation layers. Journal of Applied Physics, 2013, 113, .	1.1	30
35	Current Status and Emerging Trends in Wide Bandgap (WBG) Semiconductor Power Switching Devices. ECS Journal of Solid State Science and Technology, 2013, 2, N3055-N3063.	0.9	54
36	Dislocations as quantum wires: Buffer leakage in AlGaN/GaN heterostructures. Journal of Materials Research, 2013, 28, 1687-1691.	1.2	9

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37	Material Defects and Rugged Electrical Power Switching in Semiconductors. Materials Science Forum, 2012, 717-720, 1077-1080.	0.3	2
38	Layer-by-layer thermal conductivities of the Group III nitride films in blue/green light emitting diodes. Applied Physics Letters, 2012, 100, .	1.5	43
39	Impact of Solid State Lighting on Energy Utilization and Environmental Conditions. Transactions of the Materials Research Society of Japan, 2012, 20thAnniv, 41-45.	0.2	0
40	Microstructure of epitaxial GaN films grown on chemomechanically polished GaN(0001) substrates. Journal of Crystal Growth, 2012, 347, 88-94.	0.7	17
41	Identifying threading dislocations in GaN films and substrates by electron channelling. Journal of Microscopy, 2011, 244, 311-319.	0.8	14
42	Green Emission of Silicon Quantum Dot Light-emitting Diodes caused by Enhanced Carrier Injection. Journal of the Korean Physical Society, 2011, 59, 2183-2186.	0.3	2
43	Optical property of silicon quantum dots embedded in silicon nitride by thermal annealing. Thin Solid Films, 2010, 518, 1744-1746.	0.8	9
44	Surface and defect microstructure of GaN and AlN layers grown on hydrogen-etched 6Hâ€“SiC(0001) substrates. Acta Materialia, 2010, 58, 2165-2175.	3.8	24
45	Impact of Solid State Lighting on Energy Utilization and Environmental Conditions. Transactions of the Materials Research Society of Japan, 2010, 35, 467-471.	0.2	0
46	Enhancement of Electrical and Optical Properties of Silicon Quantum Dot Light-Emitting Diodes with ZnO Doping Layer. Japanese Journal of Applied Physics, 2009, 48, 105004.	0.8	0
47	Enhanced performance of silicon quantum dot light-emitting diodes grown on nanoroughened silicon substrate. Applied Physics Letters, 2009, 95, 073113.	1.5	14
48	Hydrogen desorption kinetics and band bending for 6Hâ€“SiC(0 0 0 1) surfaces. Surface Science, 2009, 603, 3104-3118.	0.8	27
49	On the origin of aluminum-related cathodoluminescence emissions from sublimation grown 4H-SiC(). Applied Surface Science, 2009, 255, 6535-6539.	3.1	6
50	Sequential growths of AlN and GaN layers on as-polished 6Hâ€“SiC(0001) substrates. Acta Materialia, 2009, 57, 4001-4008.	3.8	21
51	Effect of injection current density on electroluminescence in silicon quantum dot light-emitting diodes. Applied Physics Letters, 2009, 95, 153103.	1.5	5
52	Kinetics of Ga and In desorption from (7Ã—7) Si(111) and (3Ã—3) 6H-SiC(0001) surfaces. Surface Science, 2008, 602, 405-415.	0.8	13
53	Sublimation growth of an in-situ-deposited layer in SiC chemical vapor deposition on 4H-SiC(112Â¯0). Journal of Crystal Growth, 2008, 311, 72-78.	0.7	3
54	Phonon-assisted stimulated emission from pendeoepitaxy GaN stripes grown on 6H-SiC substrates. Applied Physics Letters, 2007, 91, 051119.	1.5	3

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55	Electrical and optical properties of ZnO (0001Â¯) wafers implanted with argon. Journal of Applied Physics, 2007, 101, 024902.	1.1	5
56	Growth evolution and pendeo-epitaxy of non-polar AlN and GaN thin films on 4Hâ€“SiC (112Â¯0). Journal of Crystal Growth, 2007, 300, 83-89.	0.7	10
57	Characterization of growth defects in thin GaN layers with X-ray microbeam. Physica Status Solidi (B): Basic Research, 2007, 244, 1735-1742.	0.7	6
58	Polytype Stability and Microstructural Characterization of Silicon Carbide Epitaxial Films Grown on [$$ {hbox{11}}overline{{hbox{2}}} {hbox{0}} $$]- and [0001]-Oriented Silicon Carbide Substrates. Journal of Electronic Materials, 2007, 36, 285-296.	1.0	6
59	Effect of thermal annealing on the metastable optical properties of GaN thin films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2006, 24, 1051-1054.	0.9	1
60	Ohmic Contacts to GaN. , 2006, , 489-527.		0
61	Mapping misorientation and crystallographic tilt in GaN layers via polychromatic microdiffraction. Physica Status Solidi (B): Basic Research, 2006, 243, 1508-1513.	0.7	1
62	Optimization of a Nanoparticle Suspension for Freeze Casting. Journal of the American Ceramic Society, 2006, 89, 2459-2465.	1.9	64
63	Growth and characterization of pendeo-epitaxial GaN on 4Hâ€“SiC substrates. Journal of Crystal Growth, 2006, 290, 504-512.	0.7	16
64	Growth and structural investigations of epitaxial hexagonal YMnO3 thin films deposited on wurtzite GaN(001) substrates. Thin Solid Films, 2006, 515, 1807-1813.	0.8	17
65	Growth and fabrication of AlGaN-based ultraviolet light emitting diodes on 6H-SiC(0001) substrates and the effect of carrier-blocking layers on their emission characteristics. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2006, 127, 169-179.	1.7	4
66	Origins of Parasitic Emissions from 353 nm AlGaN-based Ultraviolet Light Emitting Diodes over SiC Substrates. Japanese Journal of Applied Physics, 2006, 45, 4083-4086.	0.8	17
67	Photo-electron emission and atomic force microscopies of the hydrogen etched 6H-SiC(0001) surface and the initial growth of GaN and AlN. Applied Surface Science, 2005, 242, 428-436.	3.1	6
68	Growth of dense ZnO films via MOVPE on GaN(0001) epilayers using a low/high-temperature sequence. Journal of Crystal Growth, 2005, 277, 345-351.	0.7	12
69	Homoepitaxial growth of dense ZnO(0001) and ZnO <mml:math altimg="si1.gif" overflow="scroll" xmlns:xocs="http://www.elsevier.com/xml/xocs/dtd" xmlns:xs="http://www.w3.org/2001/XMLSchema" xmlns:xsi="http://www.w3.org/2001/XMLSchema-instance" xmlns="http://www.elsevier.com/xml/ja/dtd" xmlns:ja="http://www.elsevier.com/xml/ja/dtd" xmlns:mml="http://www.w3.org/1998/Math/MathML" xmlns:tb="http://www.elsevier.com/xml/common/table/dtd" xmlns:sb="http://www.elsevier.com/xml/common/struct-bib/dtd" xmlns:ce="http://w. Journal of Crystal	0.7	21
70	P-type doping utilizing nitrogen and Mn doping of ZnO using MOCVD for ultraviolet lasers and spintronic applications. Journal of Electronic Materials, 2005, 34, 949-952.	1.0	15
71	The formation of epitaxial hexagonal boron nitride on nickel substrates. Journal of Electronic Materials, 2005, 34, 1558-1564.	1.0	18
72	The effects of oxygen, nitrogen, and hydrogen annealing on Mg acceptors in GaN as monitored by electron paramagnetic resonance spectroscopy. Journal of Electronic Materials, 2005, 34, 34-39.	1.0	14

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73	Comparison of the microstructure and chemistry of GaN(0001) films grown using trimethylgallium and triethylgallium on AlN/SiC substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2166-2169.	0.8	1
74	White X-ray microbeam analysis of strain and crystallographic tilt in GaN layers grown by maskless pendeoepitaxy. Physica Status Solidi (A) Applications and Materials Science, 2005, 202, 732-738.	0.8	8
75	A Printable Form of Single-Crystalline Gallium Nitride for Flexible Optoelectronic Systems. Small, 2005, 1, 1164-1168.	5.2	109
76	On the microstructure of AlxGa1â^'xN layers grown on 6H-SiC(0001) substrates. Journal of Applied Physics, 2005, 97, 083501.	1.1	8
77	Preparation and characterization of atomically clean, stoichiometric surfaces of AlN(0001). Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2005, 23, 72-77.	0.9	8
78	Local strain, defects, and crystallographic tilt in GaN(0001) layers grown by maskless pendeo-epitaxy from x-ray microdiffraction. Journal of Applied Physics, 2005, 97, 013504.	1.1	9
79	Origins of Parasitic Emissions from 353 nm AlGaN-based UV LEDs over SiC Substrates. Materials Research Society Symposia Proceedings, 2005, 892, 154.	0.1	0
80	Structural TEM study of nonpolara-plane gallium nitride grown on(112Â¯0)4H-SiC by organometallic vapor phase epitaxy. Physical Review B, 2005, 71, .	1.1	193
81	Step-Controlled Strain Relaxation in the Vicinal Surface Epitaxy of Nitrides. Physical Review Letters, 2005, 95, 086101.	2.9	51
82	Intersecting basal plane and prismatic stacking fault structures and their formation mechanisms in GaN. Journal of Applied Physics, 2005, 98, 063510.	1.1	19
83	Structural defects and luminescence features in heteroepitaxial GaN grown on on-axis and misoriented substrates. Journal of Applied Physics, 2005, 97, 116101.	1.1	16
84	Structural, microstructural, and electrical properties of gold films and Schottky contacts on remote plasma-cleaned, n-type ZnO{0001} surfaces. Journal of Applied Physics, 2005, 97, 103517.	1.1	131
85	Effect of Carrier Blocking Layers on the Emission Characteristics of AlGaN-based Ultraviolet Light Emitting Diodes. Japanese Journal of Applied Physics, 2005, 44, 7254-7259.	0.8	16
86	In situcleaning of GaN(0001) surfaces in a metalorganic vapor phase epitaxy environment. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2004, 22, 2077-2082.	0.9	8
87	In situcleaning and characterization of oxygen- and zinc-terminated,n-type, ZnO{0001} surfaces. Journal of Applied Physics, 2004, 95, 5856-5864.	1.1	84
88	Surface-roughness correlations in homoepitaxial growth of GaN(0001) films by NH3 supersonic jet epitaxy. Journal of Applied Physics, 2004, 96, 4556-4562.	1.1	3
89	Selective Etching of GaN from AlGaN/GaN and AlN/GaN Structures. MRS Internet Journal of Nitride Semiconductor Research, 2004, 9, 1.	1.0	9
90	Homoepitaxial growth of (0001)- and -oriented ZnO thin films via metalorganic vapor-phase epitaxy and their characterization. Journal of Crystal Growth, 2004, 265, 390-398.	0.7	32

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91	Growth and characterization of ZnO thin films on GaN epilayers. Journal of Electronic Materials, 2004, 33, 826-832.	1.0	7
92	HVPE-GaN: comparison of emission properties and microstructure of films grown on different laterally overgrown templates. Diamond and Related Materials, 2004, 13, 1125-1129.	1.8	7
93	Growth of Homoepitaxial Films on 4H-SiC(11-20)and 8Â° Off-Axis 4H-SiC(0001) Substrates and their Characterization. Materials Science Forum, 2004, 457-460, 221-224.	0.3	2
94	Gallium nitride and related materials: challenges in materials processing. Acta Materialia, 2003, 51, 5961-5979.	3.8	59
95	Helical-type surface defects in GaN thin films epitaxially grown on GaN templates at reduced temperatures. Journal of Crystal Growth, 2003, 253, 16-25.	0.7	13
96	Surface morphology and strain of GaN layers grown using 6H-SiC(0001) substrates with different buffer layers. Journal of Crystal Growth, 2003, 253, 129-141.	0.7	42
97	Helical-type surface defects in InGaN thin films epitaxially grown on GaN templates at reduced temperatures. Thin Solid Films, 2003, 437, 140-149.	0.8	9
98	Evolution and growth of ZnO thin films on GaN(0001) epilayers via metalorganic vapor phase epitaxy. Journal of Crystal Growth, 2003, 257, 255-262.	0.7	22
99	Domain structures in 6H-SiC wafers and their effect on the microstructures of GaN films grown on A1N and A10.2Ga0.8N buffer layers. Journal of Crystal Growth, 2003, 258, 75-83.	0.7	4
100	Electron energy distribution during high-field transport in AlN. Journal of Applied Physics, 2003, 93, 2765-2771.	1.1	5
101	High performance 0.14 /spl mu/m gate-length AlGaN/GaN power HEMTs on SiC. IEEE Electron Device Letters, 2003, 24, 677-679.	2.2	15
102	Gold Schottky contacts on oxygen plasma-treated,n-type ZnO(0001Ì„). Applied Physics Letters, 2003, 82, 400-402.	1.5	378
103	Growth and Characterization of AlN and GaN Thin Films Deposited on Si(111) Substrates Containing a Very Thin Al Layer. Materials Research Society Symposia Proceedings, 2003, 798, 140.	0.1	0
104	Measurement of the band offsets of SiO2 on cleann- andp-type GaN(0001). Journal of Applied Physics, 2003, 93, 3995-4004.	1.1	83
105	Electrical and chemical characterization of the Schottky barrier formed between clean n-GaN(0001) surfaces and Pt, Au, and Ag. Journal of Applied Physics, 2003, 94, 3939-3948.	1.1	97
106	Supersonic jet epitaxy of gallium nitride using triethylgallium and ammonia. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2003, 21, 294-301.	0.9	3
107	Microscopic mapping of strain relaxation in uncoalesced pendeoepitaxial GaN on SiC. Physical Review B, 2003, 67, .	1.1	17
108	Band offset measurements of the GaNâ€‰(0001)/HfO2 interface. Journal of Applied Physics, 2003, 94, 7155-7158.	1.1	65

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109	Characterization of hydrogen etched 6Hâ€"SiC(0001) substrates and subsequently grown AlN films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2003, 21, 394-400.	0.9	15
110	Preparation and characterization of atomically clean, stoichiometric surfaces ofn- andp-type GaN(0001). Journal of Applied Physics, 2003, 94, 3163-3172.	1.1	111
111	Band offset measurements of the Si3N4/GaNâ€‰(0001) interface. Journal of Applied Physics, 2003, 94, 3949-3954.	1.1	82
112	Response to Comment on â€˜Pd growth and subsequent Schottky barrier formation on chemical vapor cleaned p-type GaN surfacesâ€™ [J. Appl. Phys. 91, 732 (2002)]. Journal of Applied Physics, 2003, 93, 3679-3679.	1.1	0
113	Electron-beam-induced optical memory effects in GaN. Applied Physics Letters, 2002, 80, 2675-2677.	1.5	14
114	Cross-sectional imaging of pendeo-epitaxial GaN using continuous-wave two-photon microphotoluminescence. Applied Physics Letters, 2002, 81, 1984-1986.	1.5	9
115	Chemical, electrical, and structural properties of Ni/Au contacts on chemical vapor cleanedp-type GaN. Journal of Applied Physics, 2002, 91, 9151-9160.	1.1	24
116	Pd growth and subsequent Schottky barrier formation on chemical vapor cleanedp-type GaN surfaces. Journal of Applied Physics, 2002, 91, 732-738.	1.1	37
117	Electrical, structural and microstructural characteristics of as-deposited and annealed Pt and Au contacts on chemical-vapor-cleaned GaN thin films. Journal of Applied Physics, 2002, 91, 2133-2137.	1.1	10
118	Probing the AlxGa1â^'xN spatial alloy fluctuation via UV-photoluminescence and Raman at submicron scale. Applied Physics Letters, 2002, 81, 4186-4188.	1.5	10
119	Strain and crystallographic tilt in uncoalesced GaN layers grown by maskless pendeoepitaxy. Applied Physics Letters, 2002, 80, 953-955.	1.5	39
120	Observations of electron velocity overshoot during high-field transport in AlN. Materials Research Society Symposia Proceedings, 2002, 743, L10.2.1.	0.1	0
121	Probing the AlxGa1-xN Atomic Distribution via UV-Photoluminescence and Raman at Sub-Î½m Scale. Materials Research Society Symposia Proceedings, 2002, 719, 8231.	0.1	0
122	Investigations regarding the maskless pendeo-epitaxial growth of GaN films prior to coalescence. IEEE Journal of Quantum Electronics, 2002, 38, 1006-1016.	1.0	20
123	TiC nanoisland formation on 6Hâ€"SiC(0001)Si. Journal of Applied Physics, 2002, 91, 6081-6084.	1.1	0
124	Strain in cracked AlGaN layers. Journal of Applied Physics, 2002, 92, 118-123.	1.1	30
125	Gallium nitride materials - progress, status, and potential roadblocks. Proceedings of the IEEE, 2002, 90, 993-1005.	16.4	34
126	Effect Of Implantation Temperature On Damage Accumulation In Ar - Implanted GaN. MRS Internet Journal of Nitride Semiconductor Research, 2002, 7, 1.	1.0	5

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127	Maskless pendeo-epitaxial growth of GaN films. Journal of Electronic Materials, 2002, 31, 421-428.	1.0	10
128	Application of Nomarski interference contrast microscopy as a thickness monitor in the preparation of transparent, SiC-based, cross-sectional TEM samples. Ultramicroscopy, 2002, 92, 265-271.	0.8	9
129	The influence of band offsets on the IV characteristics for GaN/SiC heterojunctions. Solid-State Electronics, 2002, 46, 827-835.	0.8	18
130	Growth and decomposition of bulk GaN: role of the ammonia/nitrogen ratio. Journal of Crystal Growth, 2002, 236, 529-537.	0.7	16
131	Surface instability and associated roughness during conventional and pendeo-epitaxial growth of GaN(0001) films via MOVPE. Journal of Crystal Growth, 2002, 241, 141-150.	0.7	35
132	High temperature nucleation and growth of GaN crystals from the vapor phase. Journal of Crystal Growth, 2002, 241, 404-415.	0.7	22
133	Kinetics and gas-surface dynamics of GaN homoepitaxial growth using NH3-seeded supersonic molecular beams. Surface Science, 2001, 494, 28-42.	0.8	12
134	Polarization charges and polarization-induced barriers in AlxGa1â^'xN/GaN and InyGa1â^'yN/GaN heterostructures. Applied Physics Letters, 2001, 79, 2916-2918.	1.5	12
135	Reverse-annealing phenomenon during the high-temperature implantation of Ar⁺ into GaN. Materials Research Society Symposia Proceedings, 2001, 693, 120.	0.1	2
136	Surface Instability and Associated Roughness of Pendeo-epitaxy GaN (0001) Films Grown via Metalorganic Vapor Phase Epitaxy. Materials Research Society Symposia Proceedings, 2001, 693, 359.	0.1	0
137	Removal of 6H-SiC substrate influence when evaluating GaN thin film properties via x-ray. Materials Research Society Symposia Proceedings, 2001, 693, 519.	0.1	0
138	Electron transport in AlN under high electric fields. Materials Research Society Symposia Proceedings, 2001, 693, 666.	0.1	0
139	Helical-Type Surface Defects in GaN and InGaN Thin Films Epitaxially Grown on GaN Templates at Reduced Temperatures. Materials Research Society Symposia Proceedings, 2001, 693, 69.	0.1	0
140	Review of Pendeo-Epitaxial Growth and Characterization of Thin Films of GaN and AlGaN Alloys on 6H-SiC(0001) and Si(111) Substrates. MRS Internet Journal of Nitride Semiconductor Research, 2001, 6, 1.	1.0	25
141	Ion implantation into gallium nitride. Physics Reports, 2001, 351, 349-385.	10.3	127
142	Time-Resolved Photoluminescence in Strained GaN Layers. Physica Status Solidi A, 2001, 183, 151-155.	1.7	5
143	Strain and Dislocation Reduction in Maskless Pendeo-Epitaxy GaN Thin Films. Physica Status Solidi A, 2001, 188, 729-732.	1.7	10
144	Lateral epitaxy and dislocation density reduction in selectively grown GaN structures. Journal of Crystal Growth, 2001, 222, 706-718.	0.7	66

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145	In situ cleaning of GaN/6H-SiC substrates in NH3. Journal of Crystal Growth, 2001, 222, 452-458.	0.7	13
146	Pendeo-epitaxial growth of thin films of gallium nitride and related materials and their characterization. Journal of Crystal Growth, 2001, 225, 134-140.	0.7	57
147	Conventional and pendeo-epitaxial growth of GaN(0001) thin films on Si(111) substrates. Journal of Crystal Growth, 2001, 231, 335-341.	0.7	35
148	Time-resolved spectroscopy of strained GaN/AlN/6Hâ€"SiC heterostructures grown by metalorganic chemical vapor deposition. Applied Physics Letters, 2001, 78, 1062-1064.	1.5	14
149	Optical metastability of subband gap (2.2 eV) yellow luminescence in GaN. Applied Physics Letters, 2001, 79, 281-283.	1.5	23
150	Growth of epitaxial CoSi2 on 6H-SiC(0001)Si. Journal of Applied Physics, 2001, 90, 5924-5927.	1.1	4
151	Photoluminescence and electrical characteristics of the two-dimensional electron gas in Si delta-doped GaN layers. Applied Physics Letters, 2001, 78, 1688-1690.	1.5	2
152	Hot Electron Transport in AlN. Materials Research Society Symposia Proceedings, 2000, 639, 11331.	0.1	0
153	Effect of Interface Manipulation for MBE Growth of AlN on 6H-SiC. Materials Research Society Symposia Proceedings, 2000, 622, 561.	0.1	2
154	Growth and characterization of GaN single crystals. Journal of Crystal Growth, 2000, 208, 100-106.	0.7	30
155	Crystallinity and microstructures of aluminum nitride films deposited on Si(111) substrates. Solid-State Electronics, 2000, 44, 747-755.	0.8	15
156	Optical characterization of wide bandgap semiconductors. Thin Solid Films, 2000, 364, 98-106.	0.8	10
157	Growth and microstructure of InxGa1â^'xN films grown on SiC substrates via low pressure metalorganic vapor phase epitaxy. Materials Science in Semiconductor Processing, 2000, 3, 163-171.	1.9	7
158	Pendeo-epitaxial growth of gallium nitride on silicon substrates. Journal of Electronic Materials, 2000, 29, 306-310.	1.0	21
159	Pendeo-Epitaxy^{TM} Process for Aluminum Gallium Nitride Thin Films on Silicon Carbide Substrates via Metalorganic Chemical Vapor Deposition. Materials Science Forum, 2000, 338-342, 1491-1494.	0.3	0
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